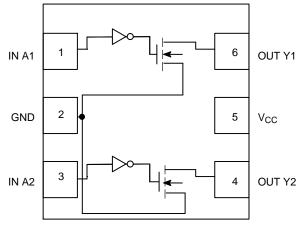
# Dual Non-Inverting Buffer, Open Drain

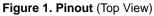
The NLX2G07 MiniGate<sup>™</sup> is an advanced high–speed CMOS dual non–inverting buffer with open drain output in ultra–small footprint.

The NLX2G07 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

# Features

- High Speed:  $t_{PD} = 2.3 \text{ ns} (Typ) @ V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \ \mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra-Small Packages
- These are Pb–Free Devices





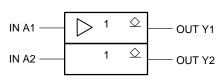


Figure 2. Logic Symbol

PIN ASSIGNMENT

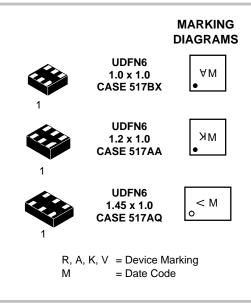
FUNCTIO	N TABLE
Α	Y
L H	L Z

		1	IN A1
		2	GND
E	, [	3	IN A2
		4	OUT Y2
		5	V <sub>CC</sub>
		6	OUT Y1



# **ON Semiconductor®**

www.onsemi.com



# ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# MAXIMUM RATINGS

Symbol	Paramet	er	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-50	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-50	mA
Ι <sub>Ο</sub>	DC Output Source/Sink Current		±50	mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100	mA	
I <sub>GND</sub>	DC Ground Current per Ground Pin	±100	mA	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Se	econds	260	°C
TJ	Junction Temperature Under Bias	150	°C	
MSL	Moisture Sensitivity	Level 1		
F <sub>R</sub>	Flammability Rating Oxygen	Index: 28 to 34	UL 94 V–0 @ 0.125 in	
ILATCHUP	Latchup Performance Above $V_{CC}$ and Below	±500	mA	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

Tested to EIA/JESD22–A114–A.
Tested to EIA/UESD22–A115–A.

4. Tested to JESD22-C101-A.

5. Tested to EIA / JESD78.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	Digital Input Voltage		0	5.5	V
V <sub>OUT</sub>	Output Voltage		0	5.5	V
T <sub>A</sub>	Operating Free–Air Temperature		-55	+125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate $V_{CC}$ = 3.3 V ± 0.3 $V_{CC}$ = 5.0 V ± 0.5	VVV	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS

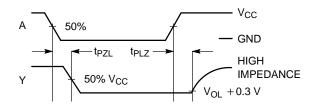
				T <sub>A</sub> = 25°C		T <sub>A</sub> = +85°C		T <sub>A</sub> = −55°C to +125°C			
Symbol Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Min	Max	Unit	
V <sub>IH</sub>	Low–Level Input Voltage		1.65– 1.95	0.75 x V <sub>CC</sub>			0.75 x V <sub>CC</sub>		0.75 x V <sub>CC</sub>		V
			2.3 to 5.5	0.70 x V <sub>CC</sub>			0.70 x V <sub>CC</sub>		0.70 x V <sub>CC</sub>		
V <sub>IL</sub>	Low–Level Input Voltage		1.65– 1.95			0.25 x V <sub>CC</sub>		0.25 x V <sub>CC</sub>		0.25 x V <sub>CC</sub>	V
			2.3 to 5.5			0.30 x V <sub>CC</sub>		0.30 x V <sub>CC</sub>		0.30 x V <sub>CC</sub>	
V <sub>OL</sub>	Low-Level Output	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu \text{A}$	1.65– 5.5			0.1		0.1		0.1	V
	Voltage	$\begin{array}{c} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 4 \text{ mA} \\ I_{OL} = 8 \text{ mA} \\ I_{OL} = 12 \text{ mA} \\ I_{OL} = 16 \text{ mA} \\ I_{OL} = 24 \text{ mA} \\ I_{OL} = 32 \text{ mA} \end{array}$	1.65 2.3 2.7 3.0 3.0 4.5		0.08 0.2 0.22 0.28 0.38 0.42	0.24 0.3 0.4 0.4 0.55 0.55		0.24 0.3 0.4 0.4 0.55 0.55		0.24 0.3 0.4 0.4 0.55 0.55	
I <sub>LKG</sub>	Z–State Output Leakage Current	$V_{IN} = V_{IH},$ $V_{OUT} = V_{CC}$ or GND	5.5			±5.0		±10		±10	μΑ
I <sub>IN</sub>	Input Leakage Current	$0 \le V_{IN} \le 5.5 V$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>OFF</sub>	Power Off Input Leakage Current	$0 \le V_{IN},$ $V_{OUT} \le 5.5 V$	0			1.0		10		10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$V_{IN} = 0 \text{ or } V_{CC}$	5.5			1.0		10		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

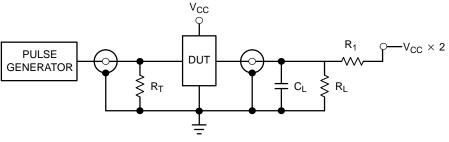
		V <sub>CC</sub>	Test	T <sub>A</sub> = 25°C			T <sub>A</sub> = -55°C to +125°C		
Symbol	Parameter	(V)	Condition	Min	Тур	Мах	Min	Max	Unit
t <sub>PZL</sub>	Propagation Delay (Figures 3 and 4)	1.65–1.95	$R_L = R_1 = 5000 \Omega,$ $C_L = 15 \text{ pF}$	1.8	5.3	11.5	1.8	12	ns
		2.3–2.7	$R_L = R_1 = 500 \Omega$ , $C_L = 50 pF$	1.2	3.7	5.8	1.2	6.4	
		3.0–3.6	$R_L = R_1 = 500 \Omega,$ $C_L = 50 \text{ pF}$	0.8	2.9	4.4	0.8	4.8	
		4.5–5.5	$R_L = R_1 = 500 \Omega,$ $C_L = 50 \text{ pF}$	0.5	2.3	3.5	0.5	3.9	
t <sub>PLZ</sub>	Propagation Delay (Figures 3 and 4)	1.65–1.95	R <sub>L</sub> = R <sub>1</sub> = 5000 Ω, C <sub>L</sub> = 15 pF	1.8	5.3	11.5	1.8	12	ns
		2.3–2.7	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	1.2	2.8	5.8	1.2	6.4	
		3.0–3.6	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	0.8	2.1	4.4	0.8	4.8	
		4.5–5.5	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	0.5	1.4	3.5	0.5	3.9	
C <sub>IN</sub>	Input Capacitance	5.5	$V_{IN} = 0 V \text{ or } V_{CC}$		2.5				pF
C <sub>OUT</sub>	Output Capacitance	5.5	$V_{IN} = 0 V \text{ or } V_{CC}$		4				pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	3.3 5.5	10 MHz V <sub>IN</sub> = 0 V or V <sub>CC</sub>		4				pF

# **AC ELECTRICAL CHARACTERISTICS** (Input $t_r = t_f = 3.0 \text{ nS}$ )

6. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.







 $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

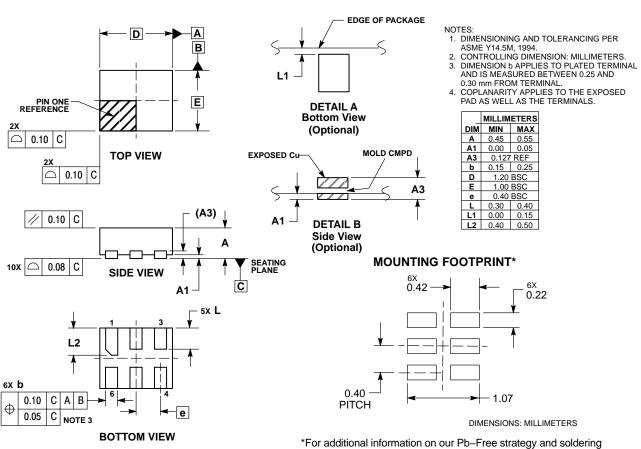
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NLX2G07MUTCG	UDFN6, 1.2 x 1.0, 0.4P (Pb–Free)	3000 / Tape & Reel
NLX2G07AMUTCG	UDFN6, 1.45 x 1.0, 0.5P (Pb–Free)	3000 / Tape & Reel
NLX2G07CMUTCG	UDFN6, 1.0 x 1.0, 0.35P (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

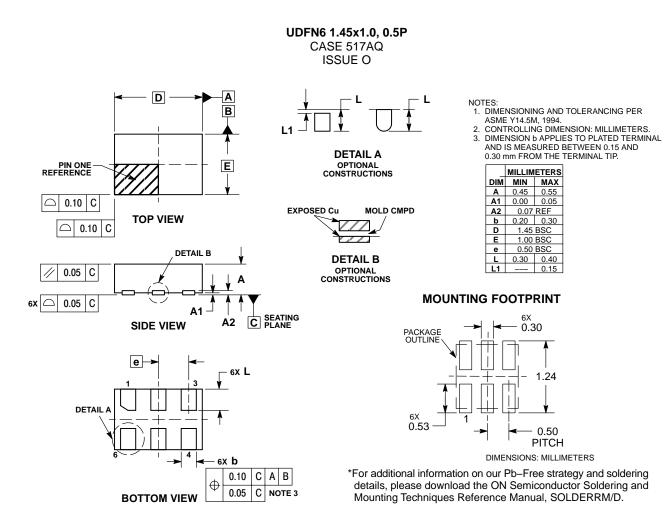
## PACKAGE DIMENSIONS

UDFN6, 1.2x1.0, 0.4P CASE 517AA ISSUE D



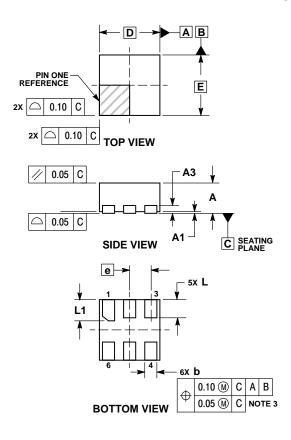
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# PACKAGE DIMENSIONS



#### PACKAGE DIMENSIONS

UDFN6 1.0x1.0, 0.35P CASE 517BX ISSUE O

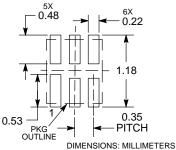


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

BURF	BURRS AND MOLD FL					
	MILLIMETERS					
DIM	MIN	MAX				
Α	0.45	0.55				
A1	0.00	0.05				
A3	0.13	REF				
b	0.12	0.22				
D	1.00	BSC				
E	1.00	BSC				
е	0.35 BSC					
L	0.25	0.35				
L1	0.30	0.40				

#### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MiniGate is a trademark of Semiconductor Components Industries, LLC (SCILLC).

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns me rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights or the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products haranges, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application. Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributor

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2010

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

NLX2G07/D